

isc Silicon NPN Power Transistor

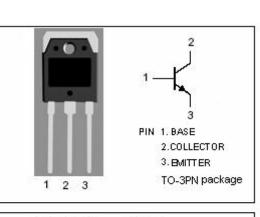
2SC3277

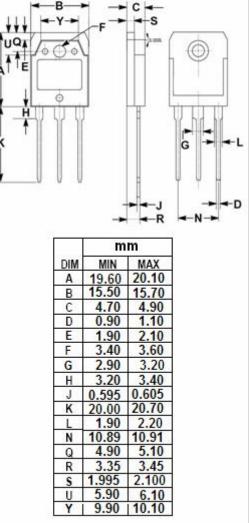
DESCRIPTION

- · High Collector-Emitter Breakdown Voltage-: V_{(BR)CEO}= 400V(Min)
- · High Switching Speed
- · Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

· Designed for switching regulator and general purpose applications.





ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

PARAMETER	VALUE	UNIT
Collector-Base Voltage	500	V
Collector-Emitter Voltage	400	V
Emitter-Base voltage	7	V
Collector Current-Continuous	10	А
Collector Current-Peak	20	А
Collector Power Dissipation @ Tc=25 $^\circ\!$	90	W
T _J Junction Temperature 150		Ĉ
Storage Temperature Range	-55~150	Ĉ
	Collector-Base Voltage Collector-Emitter Voltage Emitter-Base voltage Collector Current-Continuous Collector Current-Peak Collector Power Dissipation @ Tc=25°C Junction Temperature	Collector-Base Voltage500Collector-Emitter Voltage400Emitter-Base voltage7Collector Current-Continuous10Collector Current-Peak20Collector Power Dissipation @ Tc=25°C90Junction Temperature150



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ELECTRICAL CHARACTERISTICS

$T_{\rm C}\text{=}25^\circ\!\!{\rm C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 1mA; I _E = 0	500			V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 5mA; R _{BE} = ∞	400			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1m A; I _C = 0	7			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 6A; I _B = 1.2A			1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 6A; I _B = 1.2A			1.5	V
I _{СВО}	Collector Cutoff Current	V _{CB} = 400V ; I _E = 0			10	μA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			10	μA
h _{FE-1}	DC Current Gain	I _C = 1.2A; V _{CE} = 5V	15		50	
h _{FE-2}	DC Current Gain	I _C = 6A; V _{CE} = 5V	8			
f⊤	Current-Gain—Bandwidth Product	I _C = 1.2A; V _{CE} = 10V	15			MHz
Сов	Output Capacitance	I _E = 0; V _{CB} = 10V; f _{test} = 1.0MHz		120		pF

Switching Times

t _{on}	Turn-on Time			1.0	μ S
tstg	Storage Time	I _C = 7A, I _{B1} = -I _{B2} = 1.4A R _L = 28.6 Ω ; V _{CC} = 200V		2.5	μ S
t _f	Fall Time			1.0	μs

• h_{FE-1} Classifications

L	М	N
15-30	20-40	30-50

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